



DONGGUAN NANJING ELECTRONICS LTD.,

SOT-23 Plastic-Encapsulate Transistors

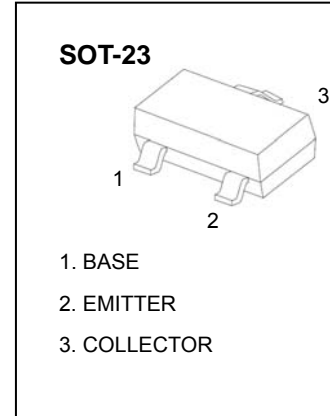
2SA1036 TRANSISTOR (PNP)

FEATURES

- Large I_C . $I_{CMax} = -500$ mA
- Low $V_{CE(sat)}$. Ideal for low-voltage operation.

MARKING : HP, HQ, HR

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)



Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-32	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -3\text{V}, I_C = -10\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.4	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -20\text{mA}, f = 100\text{MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		7		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82 - 180	120 - 270	180 - 390

B, Aug, 2012

Typical Characteristics

2SA1036

